

# FDPF6N60ZUT

## N-Channel UniFET™ II Ultra FRFET™ MOSFET

600 V, 4.5 A, 2 Ω

### Features

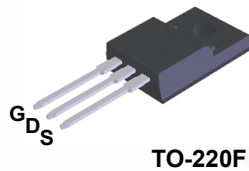
- $R_{DS(on)} = 1.7 \Omega$  (Typ.) @  $V_{GS} = 10 V$ ,  $I_D = 2.25 A$
- Low Gate Charge (Typ. 14.5 nC)
- Low  $C_{rss}$  (Typ. 5 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- RoHS Compliant

### Applications

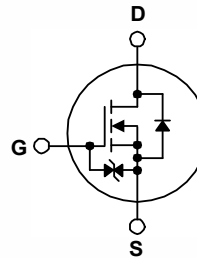
- LCD/LED TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

### Description

UniFET™ II MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. UniFET II Ultra FRFET™ MOSFET has much superior body diode reverse recovery performance. Its  $t_{rr}$  is less than 50nsec and the reverse dv/dt immunity is 20V/nsec while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore UniFET II Ultra FRFET MOSFET can remove additional component and improve system reliability in certain applications that require performance improvement of the MOSFET's body diode. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



TO-220F



### MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted.

Symbol	Parameter	FDPF6N60ZUT	Unit
$V_{DSS}$	Drain to Source Voltage	600	V
$V_{GSS}$	Gate to Source Voltage	±30	V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ C$ )	4.5*
		- Continuous ( $T_C = 100^\circ C$ )	2.7*
$I_{DM}$	Drain Current	- Pulsed (Note 1)	18*
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	150
$I_{AR}$	Avalanche Current	(Note 1)	4.5
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	10.5
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	20
$P_D$	Power Dissipation	( $T_C = 25^\circ C$ )	33.8
		- Derate Above $25^\circ C$	0.27
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ C$

\*Drain current limited by maximum junction temperature

### Thermal Characteristics

Symbol	Parameter	FDPF6N60ZUT	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.7	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDPF6N60ZUT	FDPF6N60ZUT	TO-220F	Tube	N/A	N/A	50 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}$ , $V_{GS} = 0 \text{ V}$ , $T_J = 25^\circ\text{C}$	600	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.75	-	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 600 \text{ V}$ , $V_{GS} = 0 \text{ V}$ $V_{DS} = 480 \text{ V}$ , $T_C = 125^\circ\text{C}$	-	-	25 250	$\mu\text{A}$
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}$ , $V_{DS} = 0 \text{ V}$	-	-	$\pm 10$	$\mu\text{A}$

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}$ , $I_D = 2.25 \text{ A}$	-	1.7	2.0	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 40 \text{ V}$ , $I_D = 2.25 \text{ A}$	-	3.5	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$	-	650	865	pF
$C_{oss}$	Output Capacitance		-	75	100	pF
$C_{rss}$	Reverse Transfer Capacitance		-	5	10	pF
$Q_g$	Total Gate Charge at 10V	$V_{DS} = 480 \text{ V}$ , $I_D = 4.5 \text{ A}$ , $V_{GS} = 10 \text{ V}$	-	14.5	20	nC
$Q_{gs}$	Gate to Source Gate Charge		-	4	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		(Note 4)	-	6	-

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300 \text{ V}$ , $I_D = 4.5 \text{ A}$ , $R_G = 25 \Omega$ , $V_{GS} = 10 \text{ V}$	-	19	48	ns
$t_r$	Turn-On Rise Time		-	25	60	ns
$t_{d(off)}$	Turn-Off Delay Time		-	25	60	ns
$t_f$	Turn-Off Fall Time		(Note 4)	-	45	100

### Drain-Source Diode Characteristics

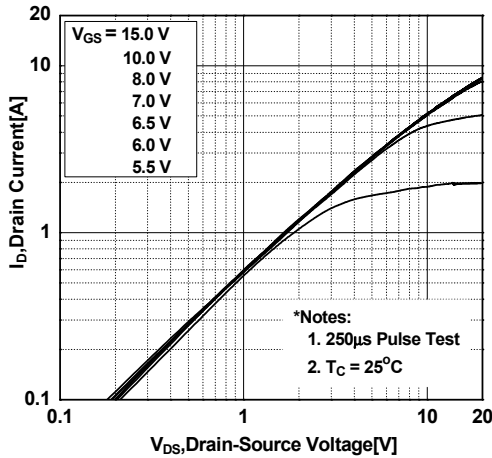
$I_S$	Maximum Continuous Drain to Source Diode Forward Current	-	-	4.5	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	18	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}$ , $I_{SD} = 4.5 \text{ A}$	-	-	1.6	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0 \text{ V}$ , $I_{SD} = 4.5 \text{ A}$ , $di_F/dt = 100 \text{ A}/\mu\text{s}$	-	36	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	37	-	nC

#### Notes:

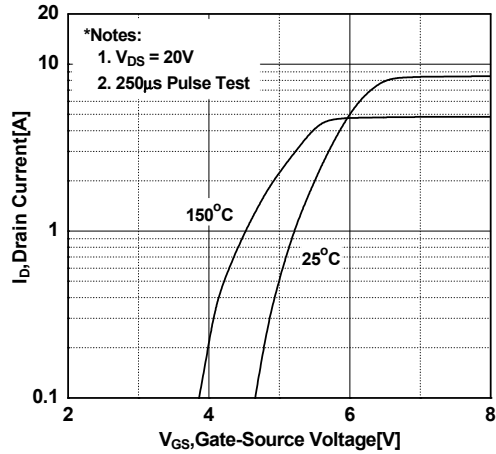
- 1: Repetitive rating; pulse-width limited by maximum junction temperature.
- 2:  $L = 15 \text{ mH}$ ,  $I_{AS} = 4.5 \text{ A}$ ,  $V_{DD} = 50 \text{ V}$ ,  $R_G = 25 \Omega$ , starting  $T_J = 25^\circ\text{C}$ .
- 3:  $I_{SD} \leq 4.5 \text{ A}$ ,  $di/dt \leq 200 \text{ A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
- 4: Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

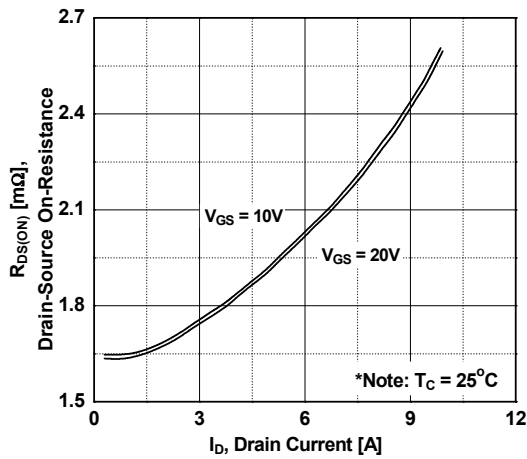
**Figure 1. On-Region Characteristics**



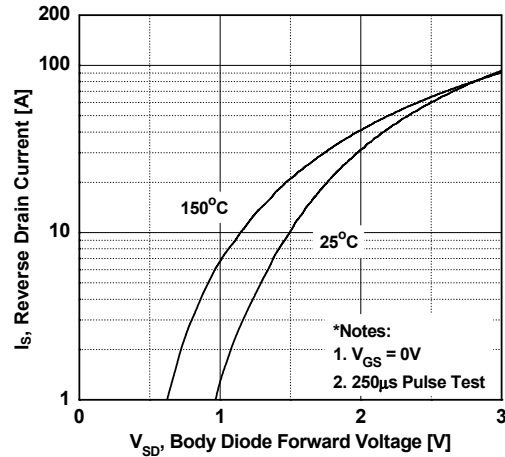
**Figure 2. Transfer Characteristics**



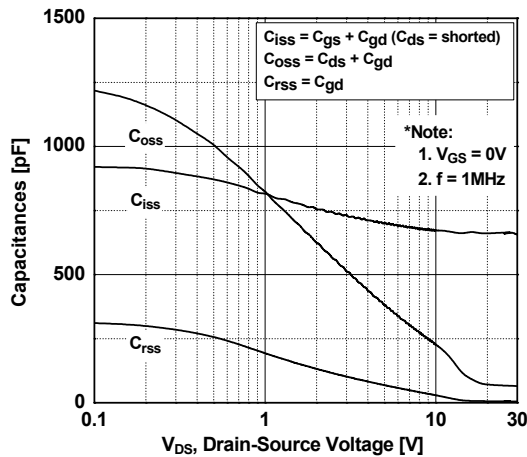
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



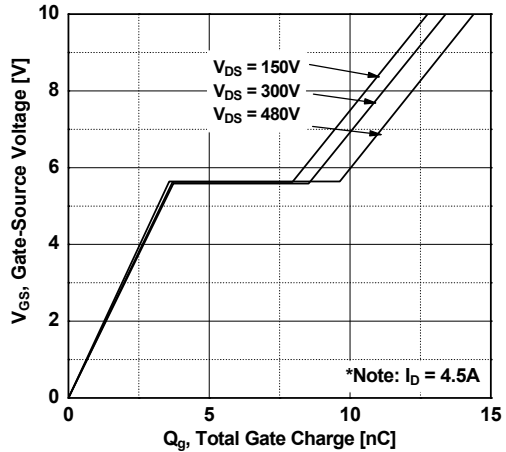
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

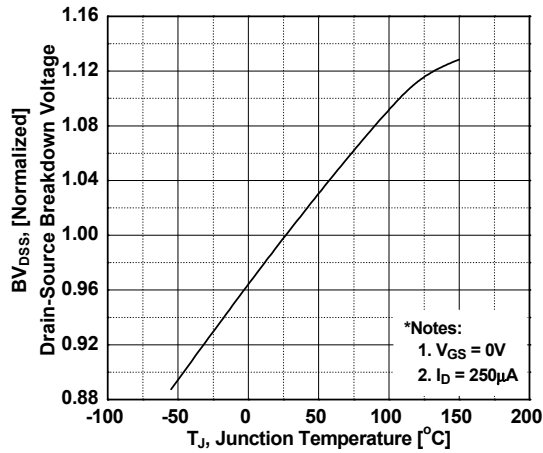


**Figure 6. Gate Charge Characteristics**

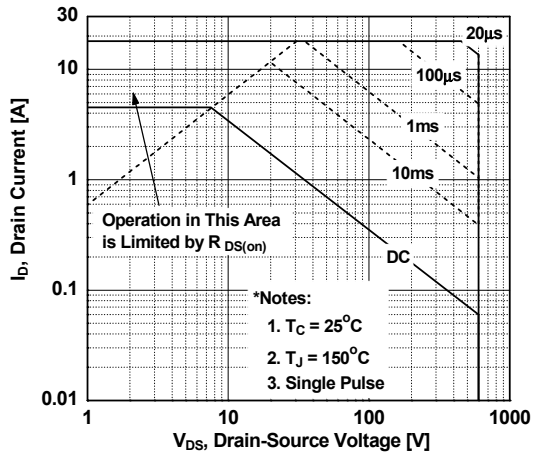


**Typical Performance Characteristics** (Continued)

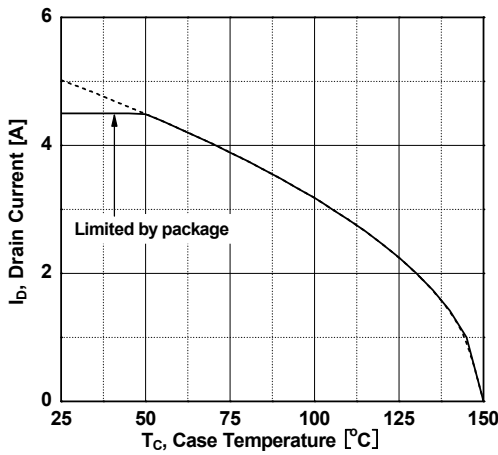
**Figure 7. Breakdown Voltage Variation vs. Temperature**



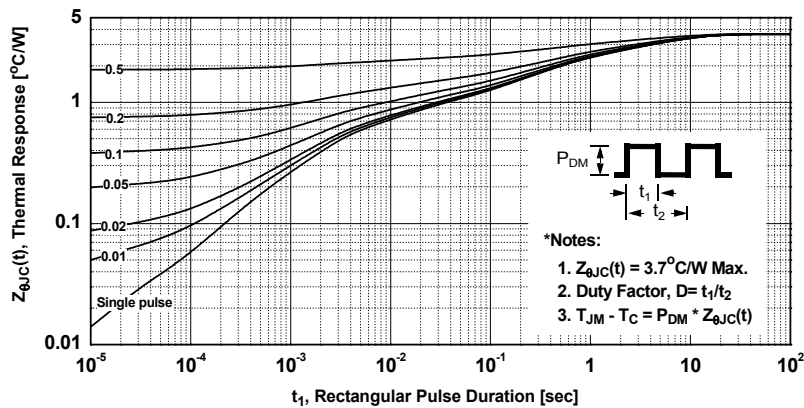
**Figure 8. Maximum Safe Operating Area**

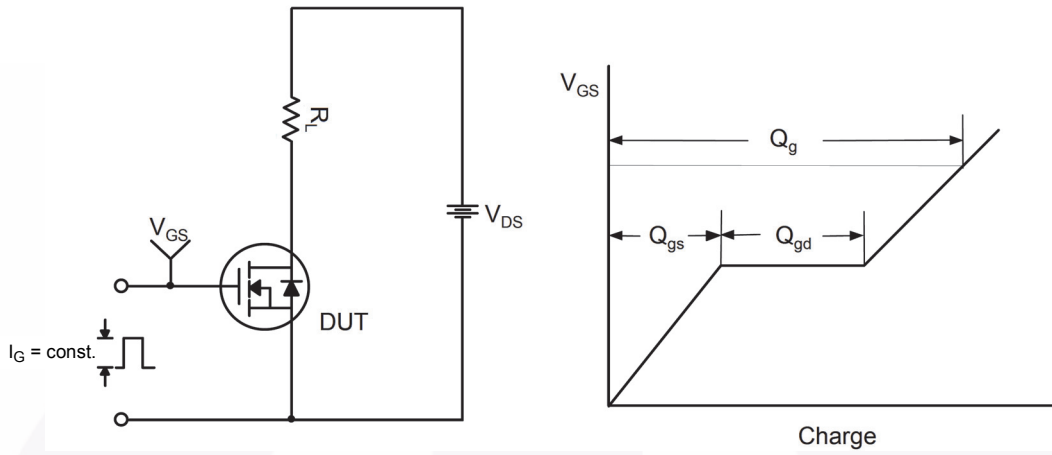


**Figure 9. Maximum Drain Current vs. Case Temperature**



**Figure 10. Transient Thermal Response Curve**





**Figure 11. Gate Charge Test Circuit & Waveform**



**Figure 12. Resistive Switching Test Circuit & Waveforms**



**Figure 13. Unclamped Inductive Switching Test Circuit & Waveforms**

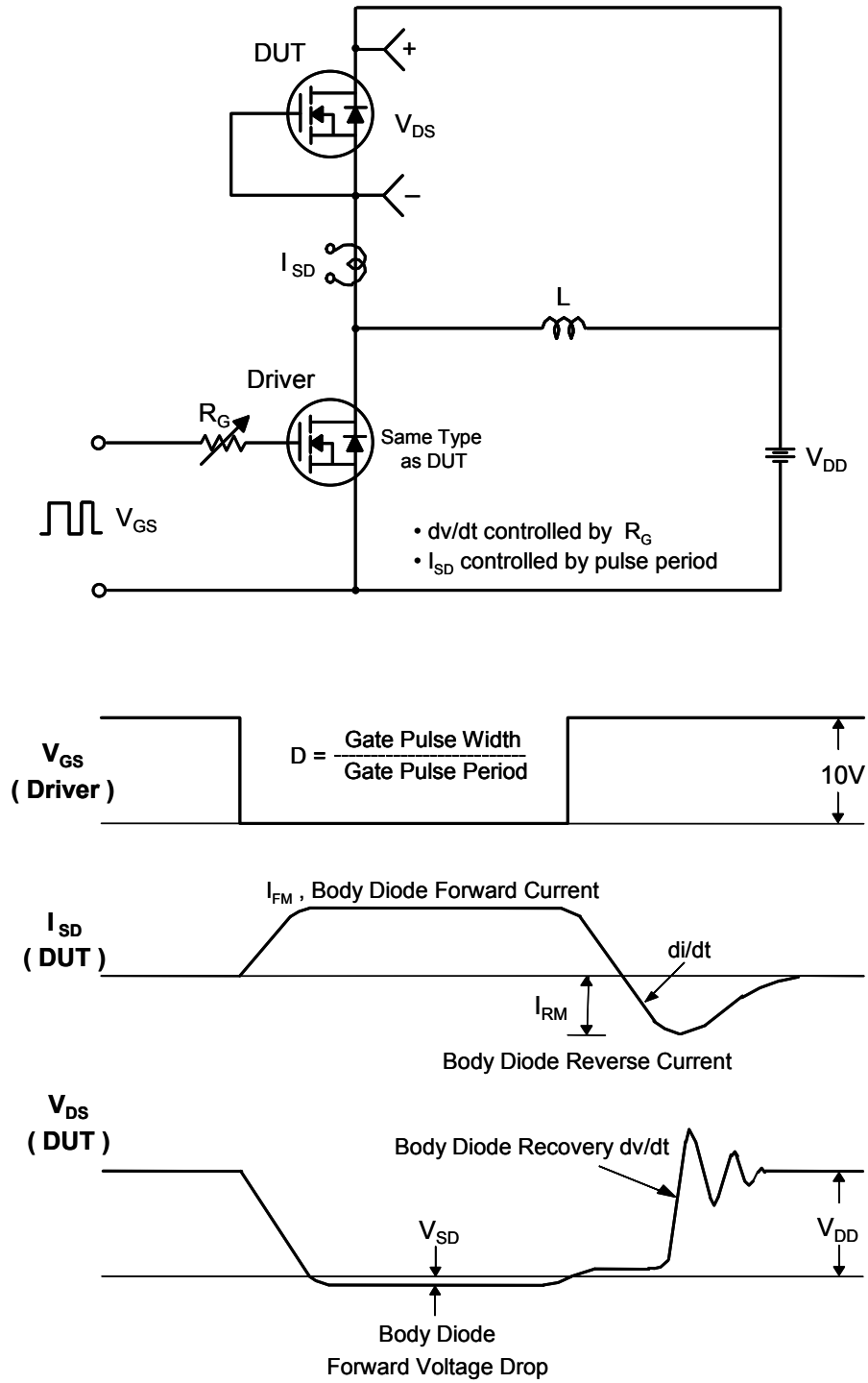
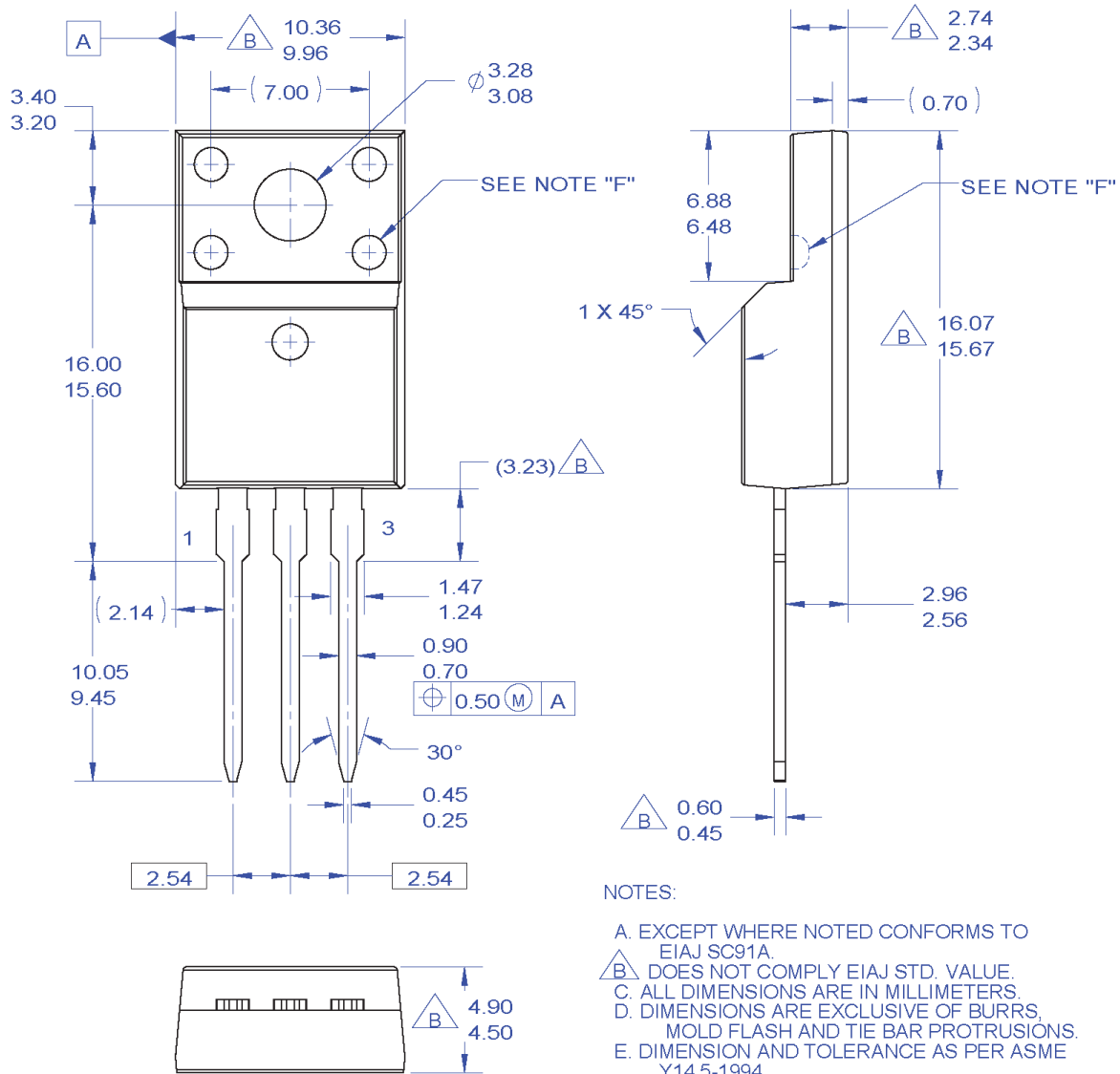


Figure 14. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

## Mechanical Dimensions



### NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. OPTION 1 - WITH SUPPORT PIN HOLE.  
OPTION 2 - NO SUPPORT PIN HOLE.
- G. DRAWING FILE NAME: TO220M03REV3

**Figure 15. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead**

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